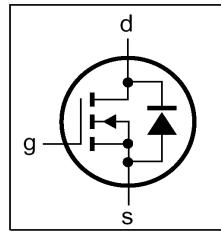


- **Ease of Paralleling**
- **Fast Switching**
- **Simple Drive Requirements**

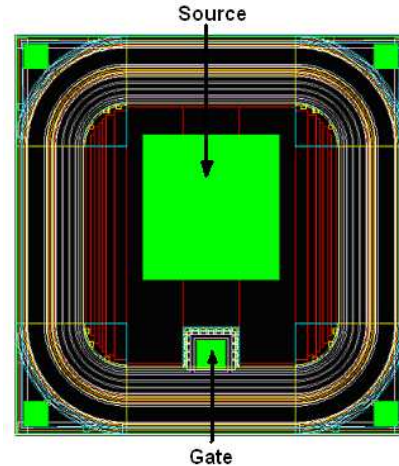


BV_{DSS}	200V
$R_{DS(ON)}$	2.0Ω
I_D	0.65A

Description

This advanced high voltage MOSFET is produced using Belling's proprietary DMOS technology. Designed for high efficiency logic level circuit.

- **Die size with scribe line** 1570 μm X 1570 μm
- **Scribe line** 80 μm
- **Die Thickness** 300 \pm 20 μm
- **Metallization**
 - Top Al
 - Bottom Ti / Ni / Ag
- **Bonding Pad Size**
 - Gate 140 μm X 102 μm
 - Source 540 μm X 540 μm
- **Passivation**



Electrical Characteristics ($T_c=25\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}, I_D=250\mu\text{A}$	200	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}, I_D=0.65\text{A}$	-	-	2.0	Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=400\mu\text{A}$	0.5	-	1.8	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=200\text{V}, V_{GS}=0\text{V}$	-	-	0.1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=20\text{V}$	-	-	10	nA
V_{SD}	Forward On Voltage	$V_{GS}=0\text{V}, I_S=0.65\text{A}$	-	-	1.2	V